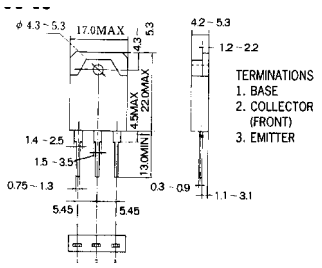
BUT56A NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE SWITCHING USE IN HORIZONTAL DEFLECTION OUTPUT STAGE

SC-65



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	1000	V
Collector-EmitterVoltage	VCEO	450	V
Emitter-Base voltage	VEBO	6	V
Collector Current (DC)	IC	8	A
Collector Peck Current	ICM	10	A
Base Current (DC)	IB	4	A
Collector Dissipation (Tc=25°C)	PC	100	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characterristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current (VBE=0)	ICES	VCE= 800V , VEB= 0			5	mA
Emitter Cutoff Current(IC=0)	IEBO	VEB= 6V , IC=0			1	mA
Collector Emitter Saturation Voltage	VCE(sat)	IC=5A, IB=0.5A			2.5	V
Base- Emitter Saturation Voltage	VBE(sat)	IC=5A, IB=1.2A			2.5	V
Current Gain Bandwith Product	fT	VCE= 10V , IC=500mA	10			MHZ
Turn-Off Time	toff	IC=4A, IB=0.4A			0.75	µS
		IC=4A, IB=0.6A			0.5	µS
		IC=5A, IB=1.0A			0.5	µS

Wing Shing Computer Components Co., (H.K.)Ltd. Tel:(852)2341 9276 Fax:(852)2797 8153
Homepage: http://www.wingshing.com E-mail: wsccltd@hkstar.com